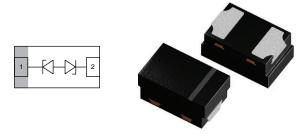


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Single-Line Bidirectional ESD-Protection Diode in DFN1006-2B



MARKING (example only)



Bar = pin 1 marking X = date code YY = type code (see table below)

LINKS TO ADDITIONAL RESOURCES



PICE	
Models	Apr
	_

FEATURES

- Compact DFN1006-2B package
- Low package height < 0.5 mm
- 1-line bidirectional ESD-protection
- AEC-Q101 qualified available
- Working range ±14 V; ± 28 V
- ESD immunity acc. IEC 61000-4-2 ±15 kV to ±30 kV contact discharge ±15 kV to ±30 kV air discharge
- Lead plating: Sn (e3) - Soldering can be checked by standard vision inspection
 - AOI = Automated Optical Inspection
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Soldering Recommendations for DFN Packages: please see Application Note: www.vishay.com/doc?86198

ORDERING INFORMATION							
		ENVIRONMEN					
PART NUMBER AEC-Q10 (EXAMPLE) QUALIFIE				10K PER 7" REEL (8 mm TAPE)	ORDERING CODE (EXAMPLE)		
		GREEN		MOQ = 10K/BOX			
VMMBZ16C1DD1	-	G	3	-08	VMMBZ16C1DD1-G3-08		
VMMBZ16C1DD1	Н	G	3	-08	VMMBZ16C1DD1HG3-08		

PACKAGE DATA								
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS		
VMMBZ16C1DD1	DFN1006-2B	2Y	0.83 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
VMMBZ33C1DD1	DFN1006-2B	2N	0.83 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		





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PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	4	А
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot ⁽¹⁾	P _{PP}	108	W
Peak pulse current	t _p = 10/1000 μs ⁽¹⁾	I _{PPM}	0.65	А
Peak pulse power	t _p = 10/1000 μs ⁽¹⁾	P _{PP}	15	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses (1)	M	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses ⁽¹⁾	V _{ESD}	30	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VMMBZ33C1DD1 (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	1.7	А			
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot ⁽¹⁾	P _{PP}	100	W			
Peak pulse current	t _p = 10/1000 μs ⁽¹⁾	I _{PPM}	0.3	А			
Peak pulse power	t _p = 10/1000 μs ⁽¹⁾	P _{PP}	15	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses (1)	V	15	kV			
	Air discharge acc. IEC 61000-4-2; 10 pulses ⁽¹⁾	V _{ESD}	15	kV			
Operating temperature	Junction temperature	ТJ	-55 to +150	°C			
Storage temperature		T _{stg}	-55 to +150	°C			

ELECTRICAL CHARACTERISTICS VMMBZ16C1DD1 (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	14	V		
Reverse voltage	At I _R = 0.01 μA	V _R	14	-	-	V		
Reverse current	At V _R = 14 V	I _R	-	< 0.001	0.01	μA		
	At $V_R = 14$ V; $T_J = 150$ °C ⁽¹⁾		-	0.06	10	μA		
Reverse breakdown voltage	At I _R = 1 mA	V _{BR}	16.2	16.7	17.3	V		
	At $I_R = 1$ mA; $T_J = -40$ °C to +150 °C ⁽¹⁾		15	-	18.7	V		
Reverse clamping voltage	At I _{PP} = I _{PPM} = 4 A, t _p = 8/20 μs	V _C	20	23.7	27	V		
	t _p = 100 ns (TLP); I _{TLP} = 16 A ⁽¹⁾	V _{C_TLP}	-	26	-	V		
Dynamic resistance	$t_p = 100 \text{ ns} (\text{TLP})^{(1)}$	r _{dyn}	-	0.55	-	Ω		
Capacitance	At $V_R = 0 V$; f = 1 MHz	C _D	12	14.5	17	pF		

ELECTRICAL CHARACTERISTICS VMMBZ33C1DD1 (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	28	V		
Reverse voltage	At I _R = 0.01 μA	V _R	28	-	-	V		
Deverse everent	At V _R = 28 V	I _R	-	< 0.001	0.01	μA		
Reverse current	At $V_R = 28 \text{ V}; \text{ T}_J = 150 \text{ °C}^{(1)}$		-	0.1	10	μA		
Reverse breakdown voltage	At I _R = 1 mA	V _{BR}	32.7	33.7	34.8	V		
	At $I_R = 1$ mA; $T_J = -40$ °C to +150 °C ⁽¹⁾		30	-	39.7	V		
Reverse clamping voltage	At I _{PP} = I _{PPM} = 1.7 A, t _p = 8/20 μs	V _C	40	49	59	V		
	t _p = 100 ns (TLP); I _{TLP} = 16 A ⁽¹⁾	V _{C_TLP}	-	88	-	V		
Dynamic resistance	t _p = 100 ns (TLP) ⁽¹⁾	r _{dyn}	-	3.3	-	Ω		
Capacitance	At $V_R = 0$ V; f = 1 MHz	CD	6	8	10	pF		

Note

⁽¹⁾ Guaranteed by design. Tested during device characterization



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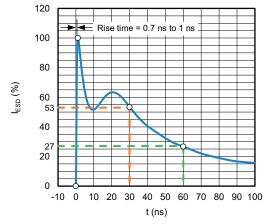


Fig. 1 - ESD Discharge Current Wave Form Acc. IEC 61000-4-2 (330 Ω / 150 pF)

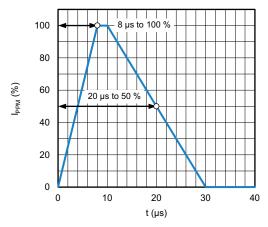


Fig. 2 - 8/20 µs Peak Pulse Current Wave Form Acc. IEC 61000-4-5

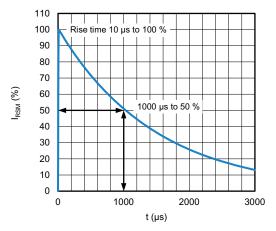


Fig. 3 - 10/1000 µs Peak Pulse Current Wave Form

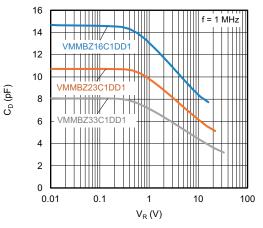


Fig. 4 - Typical Capacitance vs. Reverse Voltage

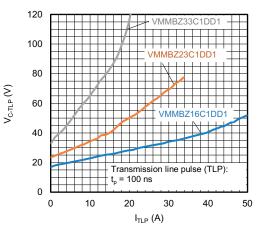


Fig. 5 - Typical Clamping Voltage vs. Peak Pulse Current

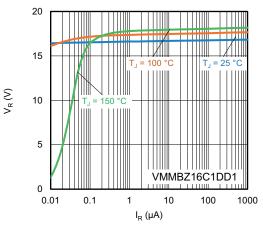


Fig. 6 - Typical Reverse Voltage vs. Reverse Current

Rev. 1.3, 05-Jun-2024

3 estions contact: ESDprotection Document Number: 86193

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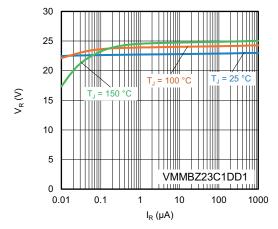


Fig. 7 - Typical Reverse Voltage vs. Reverse Current

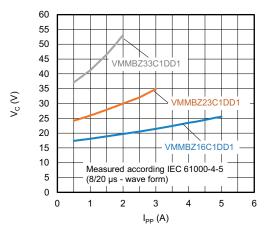


Fig. 8 - Typical Peak Clamping Voltage vs. Peak Pulse Current

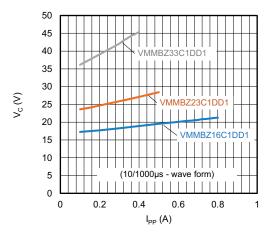


Fig. 9 - Typical Peak Clamping Voltage vs. Peak Pulse Current

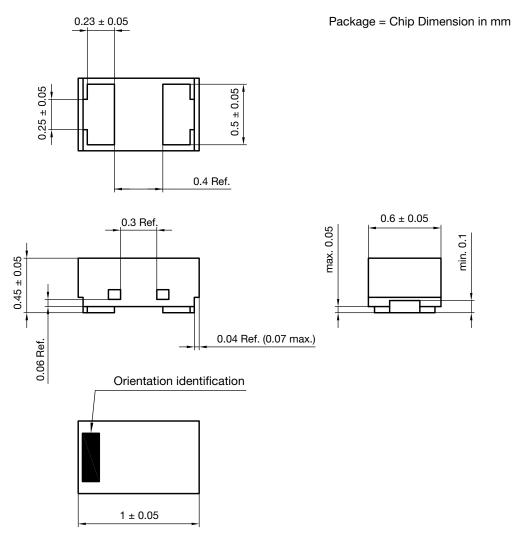
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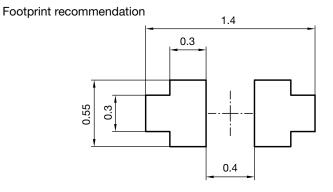
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PACKAGE DIMENSIONS in millimeters (inches): DFN1006-2B





Document no.: S8-V-3906.04-059 (4) Created - Date: 11-Jul-2018 Rev.5 - Date: 17-Sep-2021

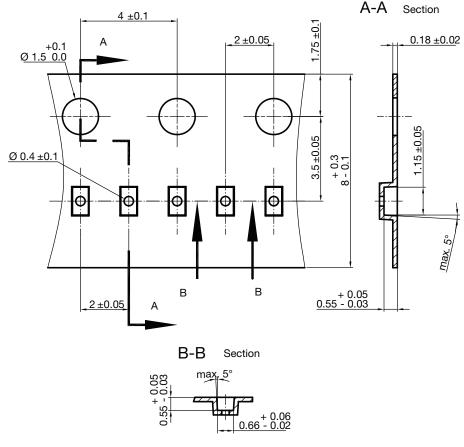
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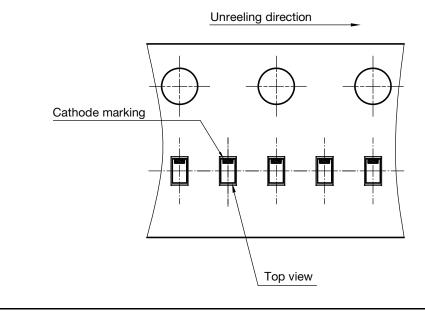
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CARRIER TAPE DFN1006-2B



S8-V-3906.04-063 (4) created 28.10.2019 surface resistance: $10^5 - 10^{11} \frac{OHMS}{SQ}$ Cummulative tolerances of 10 sprocket holes is ± 0.2 mm

ORIENTATION IN CARRIER TAPE DFN1006-2B



Rev. 1.3, 05-Jun-2024

S8-V-3906.04-064 (4)

created 28.10.2019



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